

Date: - 1 June, 2018

Data Sheet Issue:- A1

## **Advance Data**

# Insulated Gate Bi-Polar Transistor Type T1000TC33E

# **Absolute Maximum Ratings**

	VOLTAGE RATINGS	MAXIMUM LIMITS	UNITS
$V_{CES}$	Collector – emitter voltage	3300	V
$V_{DC\ link}$	Permanent DC voltage for 100 FIT failure rate	1800	V
$V_{GES}$	Peak gate – emitter voltage	±20	V

	RATINGS	MAXIMUM LIMITS	UNITS
I <sub>C(DC)</sub>	DC collector current, IGBT	1000	Α
I <sub>CRM</sub>	Repetitive peak collector current, t <sub>p</sub> =1ms, IGBT	2000	Α
I <sub>ECO</sub>	Maximum reverse emitter current, t <sub>p</sub> =100µs, (note 2 & 3)	1000	Α
P <sub>MAX</sub>	Maximum power dissipation, IGBT (Note 2)	6.4	kW
Tj	Operating temperature range.	-40 to +125	°C
T <sub>stg</sub>	Storage temperature range.	-40 to +125	°C

#### Notes: -

- 1) Unless otherwise indicated  $T_j = 125$ °C.
- 2)  $T_{sink} = 25$ °C, double side cooled.
- 3) Maximum commutation loop inductance 200nH.



# **Characteristics**

## **IGBT** Characteristics

	PARAMETER	MIN	TYP	MAX	TEST CONDITIONS	UNITS
\/	Collector emitter esturation valtage	-	2.57	2.97	I <sub>C</sub> = 1000A, V <sub>GE</sub> = 15V, T <sub>j</sub> = 25°C	V
V <sub>CE(sat)</sub>	Collector – emitter saturation voltage	-	3.40	3.80	I <sub>C</sub> = 1000A, V <sub>GE</sub> = 15V	V
$V_{T0}$	Threshold voltage	-	-	1.835	Current range: 333A – 1000A	V
$r_{T}$	Slope resistance	-	-	1.969	Current range: 333A = 1000A	mΩ
$V_{\text{GE(TH)}}$	Gate threshold voltage	-	5.3	-	$V_{CE} = V_{GE}$ , $I_C = 85mA$	V
I <sub>CES</sub>	Collector – emitter cut-off current	-	5	25	V <sub>CE</sub> = V <sub>CES</sub> , V <sub>GE</sub> = 0V	mA
I <sub>GES</sub>	Gate leakage current	-	-	±10	$V_{GE} = \pm 20V$	μΑ
Cies	Input capacitance	-	135	-	$V_{CE} = 25V$ , $V_{GE} = 0V$ , $f = 1MHz$ , $T_j = 25$ °C	nF
$t_{d(on)}$	Turn-on delay time	-	1.7	-		μs
$t_r(V)$	Rise time	-	1.8	-		μs
$Q_{g(on)}$	Turn-on gate charge	-	21	-	I <sub>C</sub> =1000A, V <sub>CE</sub> =1800V, di/dt=2000A/μs	μC
E <sub>on</sub>	Turn-on energy	-	2.6	-	$V_{GE} = \pm 15V, L_s = 200nH$	J
$t_{\text{d(off)}}$	Turn-off delay time	-	5.3	-	$R_{g(ON)}$ = 2.2 $\Omega$ , $R_{g(OFF)}$ = 15 $\Omega$ , $C_{GE}$ =430nF	μs
$t_f(I)$	Fall time	-	1.5	-	Freewheel diode type EX574MC33E at T <sub>i</sub> =125°C	μs
$Q_{g(off)}$	Turn-off gate charge	-	13	-	, , , , , , , , , , , , , , , , , , , ,	μC
E <sub>off</sub>	Turn-off energy	-	2.7	-		J
I <sub>SC</sub>	Short circuit current	-	3000	-	$V_{GE}$ =+15V, $V_{CC}$ =1800V, $V_{CEmax}$ $\leq$ $V_{CES}$ , $t_p$ $\leq$ 10 $\mu$ s	А

#### Thermal Characteristics

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	PARAMETER	MIN	TYP	MAX	TEST CONDITIONS	UNITS
		-	-	15.6	Double side cooled	K/kW
$R_{thJK}$	Thermal resistance junction to sink, IGBT	-	-	25.6	Collector side cooled	K/kW
		-	-	40.6	Emitter side cooled	K/kW
F	Mounting force	15	-	25	Note 2	kN
$W_t$	Weight	-	1.2	-		kg

#### Notes:-

- 1) Unless otherwise indicated T<sub>j</sub>=125°C.
- 2) Consult application note 2008AN01 for detailed mounting requirements
- 3) C<sub>GE</sub> is additional gate emitter capacitance added to output of gate drive



## **Curves**

Figure 1 – Typical collector-emitter saturation voltage characteristics

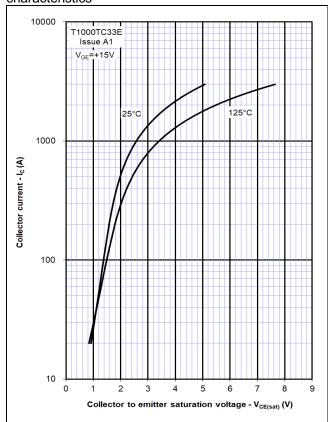


Figure 3 – Typical output characteristic

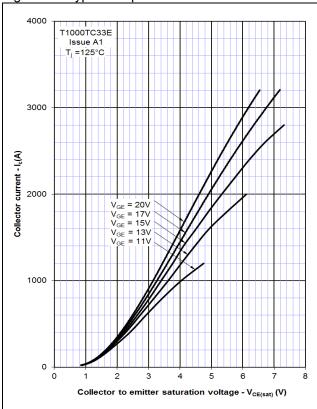


Figure 2 – Typical output characteristic

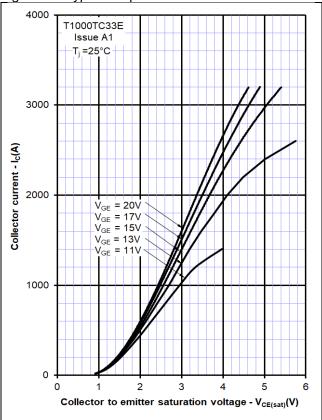


Figure 4 – Typical turn-on delay time vs gate resistance

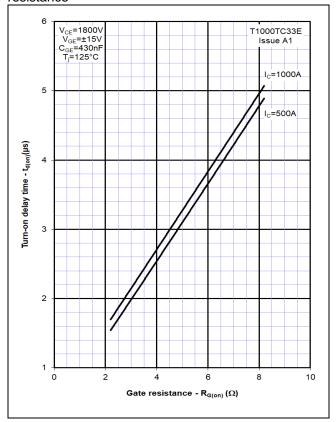




Figure 5 – Typical turn-off delay time vs. gate resistance

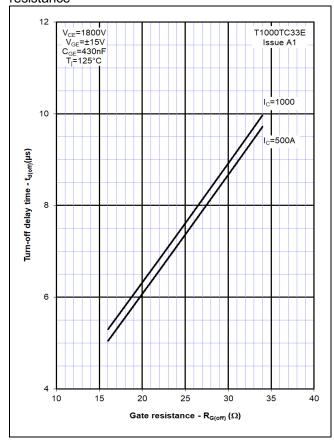


Figure 6 – Typical turn-on energy vs. collector current

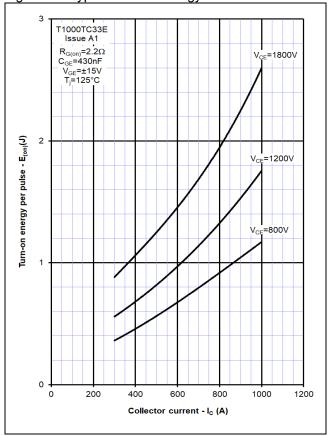


Figure 7 - Typical turn-on energy vs. di/dt

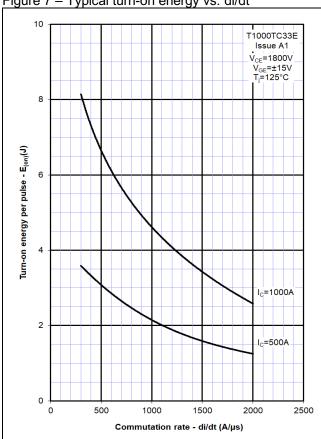


Figure 8 – Typical turn-off energy vs. collector current

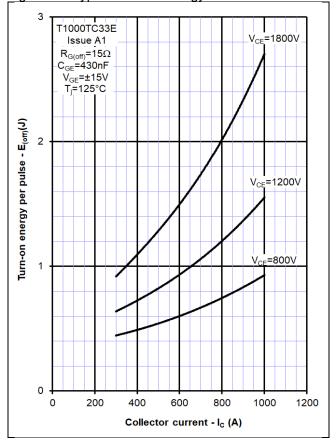




Figure 9 - Turn-off energy vs voltage

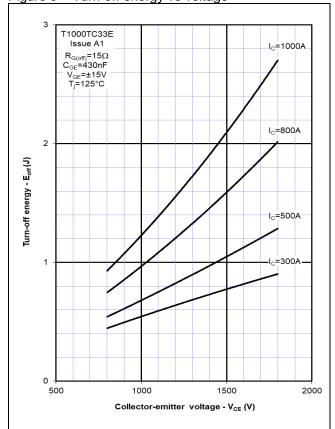


Figure 10 – Safe operating area

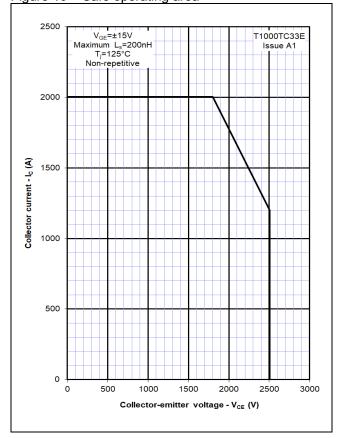
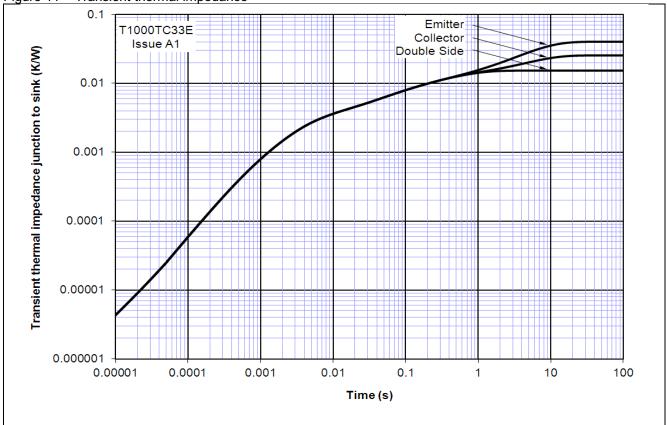
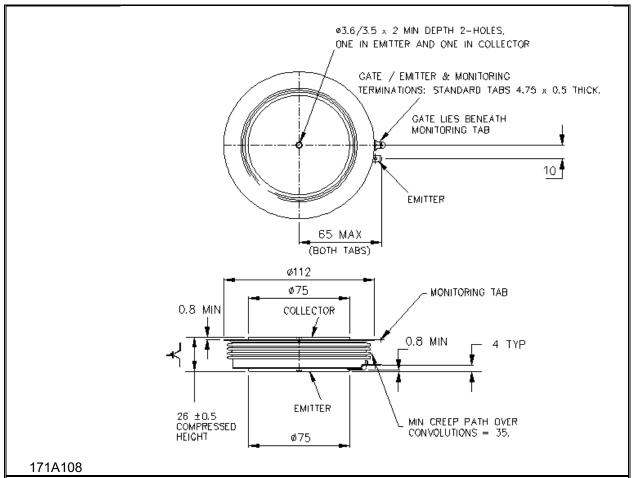


Figure 11 – Transient thermal impedance





# **Outline Drawing & Ordering Information**



ORDERING INFORMATION

(Please quote 10 digit code as below)

, , , , , , , , , , , , , , , , , , , ,							
T1000	TC	33	E				
Fixed type Code	Fixed Outline Code	Voltage Grade V <sub>CES</sub> /100 33	Fixed format code				

Typical order code: T1000TC33E (V<sub>CES</sub> = 3300V)

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